

DESCRIPTION

The MX3401A uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

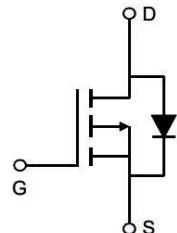
GENERAL FEATURES

- $V_{DS}=-30V$, $I_D=-4.2A$
- $R_{DS(ON)}(\text{Typ.})=60\text{m}\Omega$ @ $V_{GS}=-2.5V$
- $R_{DS(ON)}(\text{Typ.})=50\text{m}\Omega$ @ $V_{GS}=-4.5V$
- $R_{DS(ON)}(\text{Typ.})=45\text{m}\Omega$ @ $V_{GS}=-10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

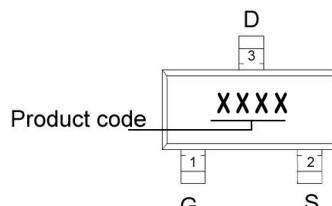
APPLICATION

- PWM applications
- Load switch
- Power management

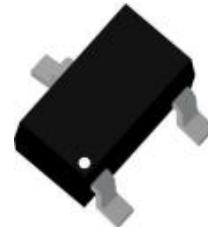
PINOUT



Schematic diagram



Marking and pin Assignment



SOT-23 top view

ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MX3401A	-55°C to 150°C	SOT-23	-

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-4.2	A
Pulsed Drain Current ^(Note1)	I_{DM}	-30	A
Maximum Power Dissipation	P_D	1.3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	95	°C/W
--	-----------------	----	------

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.


ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
-----------	--------	------------	-----	-----	-----	------

Off Characteristics

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA

On Characteristics^(Note 3)

Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.7	-0.9	-1.3	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-1\text{A}$	-	60	100	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$	-	50	65	$\text{m}\Omega$
		$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-4.2\text{A}$	-	45	50	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-4.2\text{A}$	-	10	-	S

Dynamic Characteristics^(Note 4)

Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	950	-	pF
Output Capacitance	C_{oss}		-	115	-	pF
Reverse Transfer Capacitance	C_{rss}		-	75	-	pF

Switching Characteristics^(Note 4)

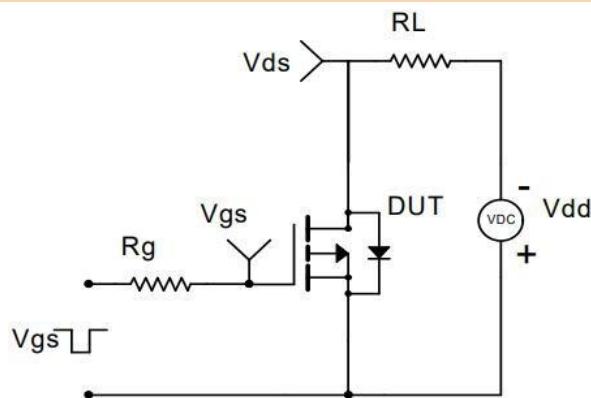
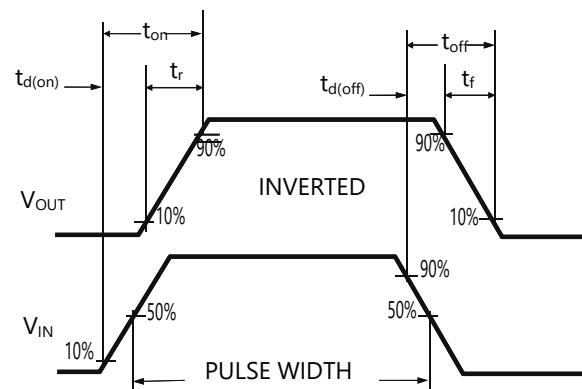
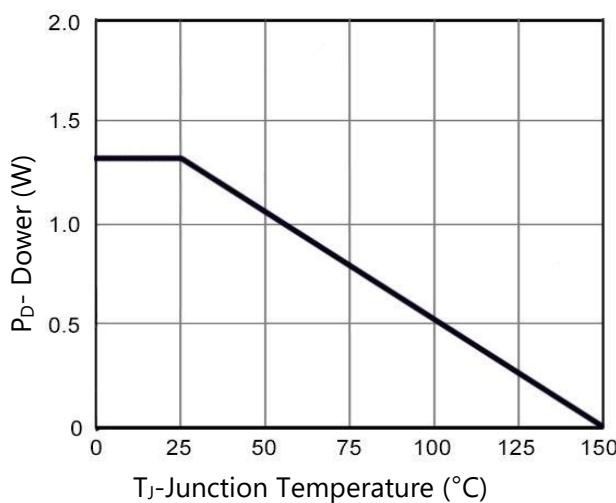
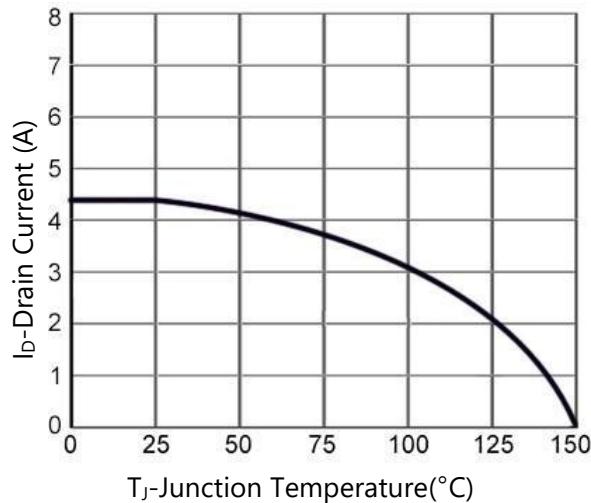
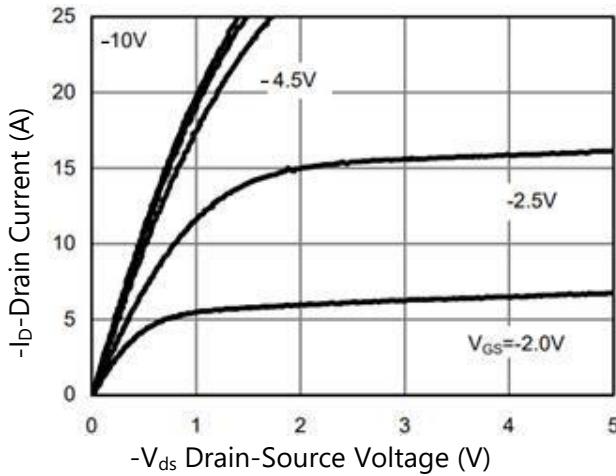
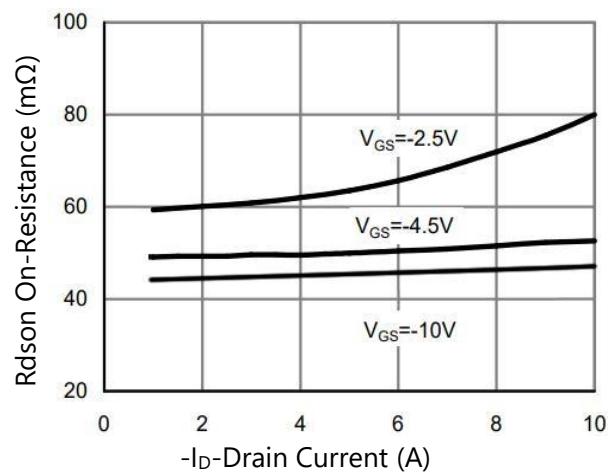
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-15\text{V}, I_{\text{D}}=-3.2\text{A}, R_{\text{L}}=1\Omega, V_{\text{GS}}=-10\text{V}, R_{\text{G}}=3\Omega$	-	7	-	nS
Turn-on Rise Time	t_{r}		-	3	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	30	-	nS
Turn-Off Fall Time	t_{f}		-	12	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4\text{A}, V_{\text{GS}}=-10\text{V}$	-	13	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC

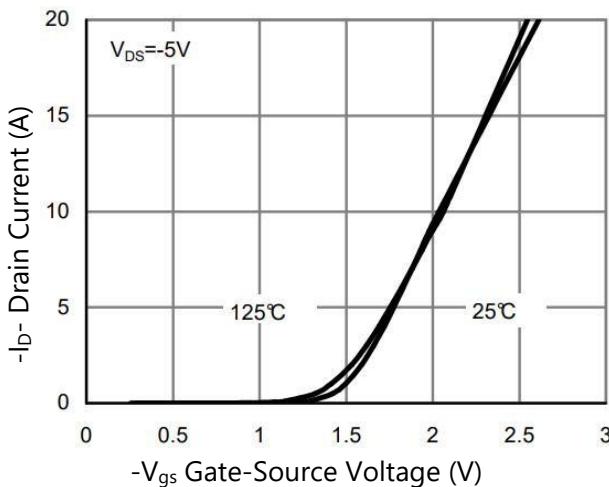
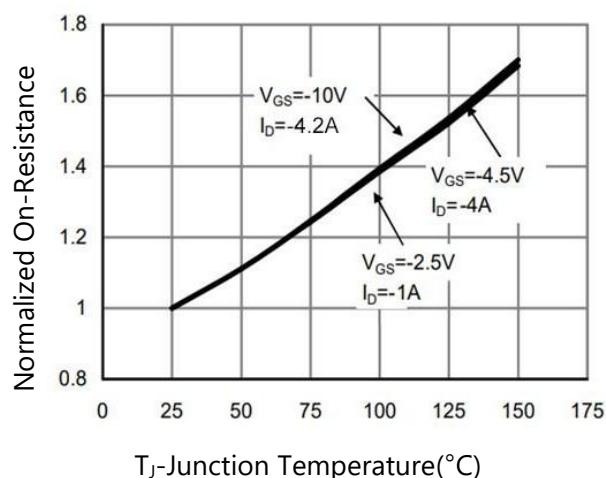
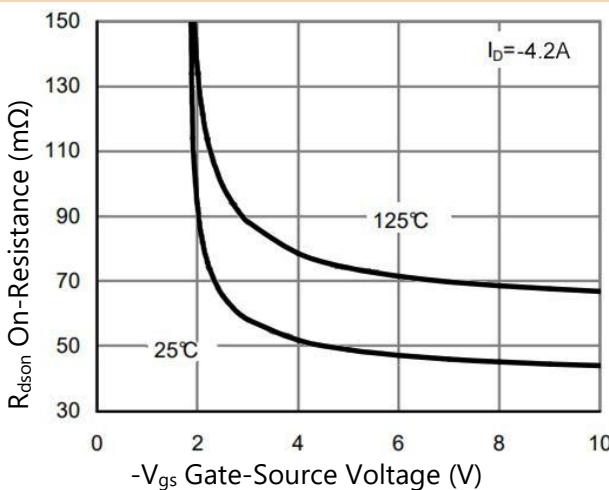
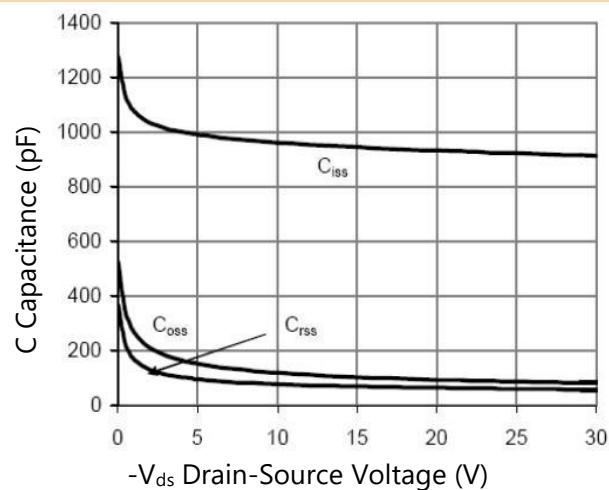
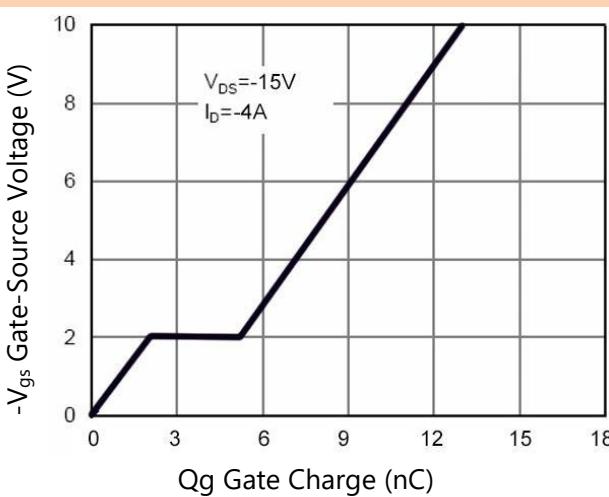
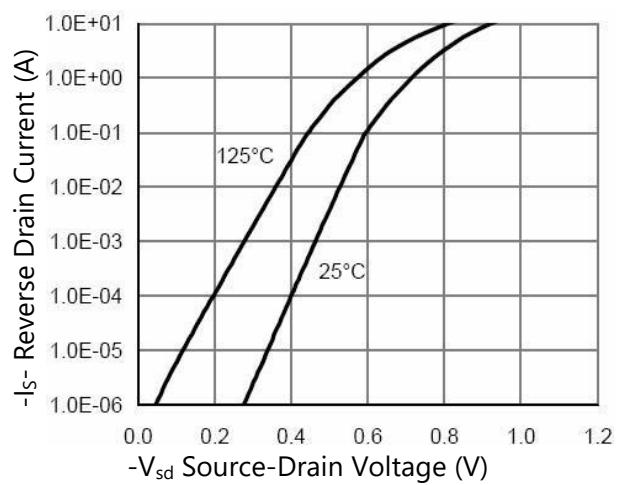
Drain-Source Diode Characteristics

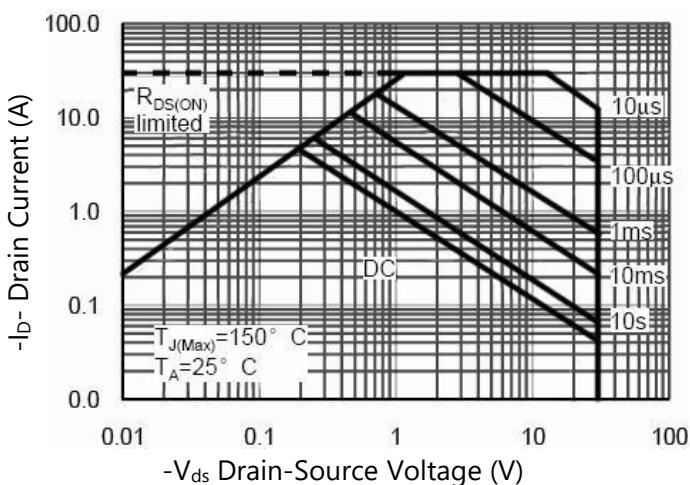
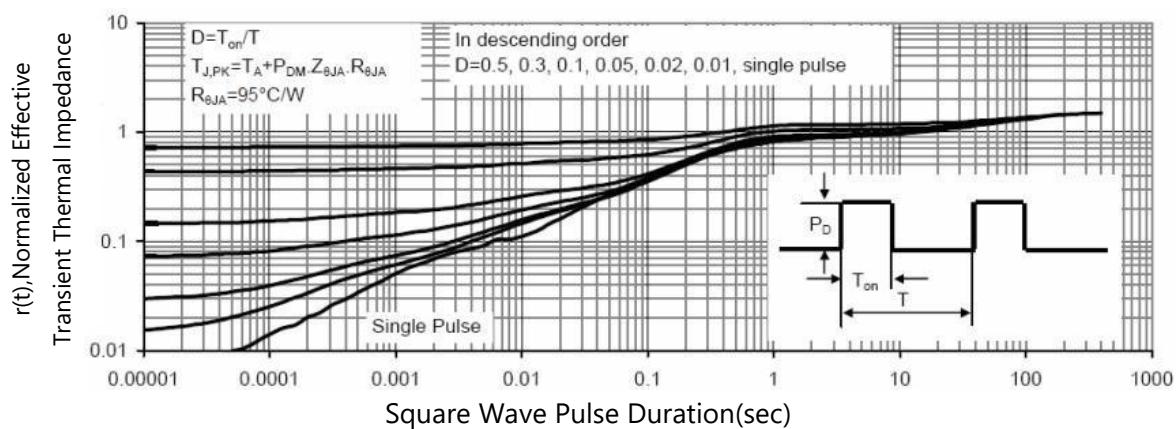
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-1\text{A}$	-	-	-1.2	V
Diode Forward Current ^(Note 2)	I_{S}		-	-	-2	A

Note 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

Note 4. Guaranteed by design, not subject to product.

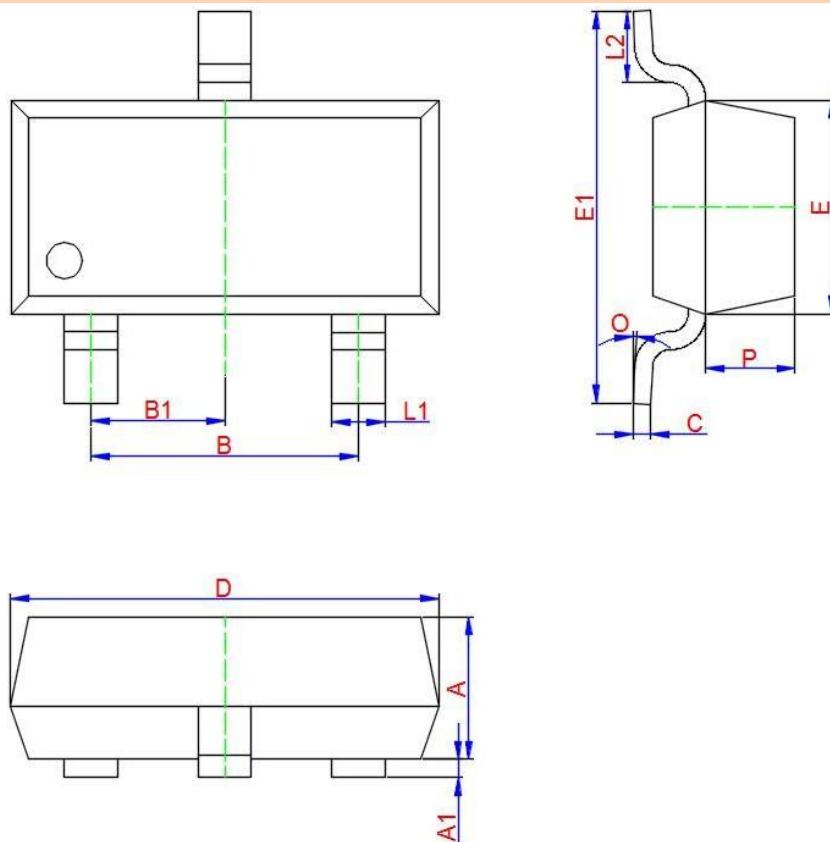

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

Figure 3. Power De-rating

Figure 4. Drain Current

Figure 5. Output Characteristics

Figure 6. Rdson vs Drain Current



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 7. Transfer Characteristics

Figure 8. R_{DSON} vs Junction Temperature

Figure 9. R_{DSON} vs V_{gs}

Figure 10. Capacitance vs V_{ds}

Figure 11. Gate Charge

Figure 12. Source- Drain Diode Forward



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 13. Safe Operation Area

Figure 14. Normalized Maximum Transient Thermal Impedance


PACKAGE INFORMATION

SOT-23



Symbol	Dimensions In Millimeters		
	Min	Max	Min
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
B	1.800	1.900	2.000
B1	0.950 TYP.		
L2	0.200	0.350	0.450
P	0.550	0.575	0.600
O	0°	4°	8°